







**BQ77216** 

# BQ77216 Voltage and Temperature Protection for 3-Series to 16-Series Cell Li-Ion **Batteries with Internal Delay Timer**

#### 1 Features

- 3-series cell to 16-series cell protection
- High-accuracy over voltage protection
  - ± 10 mV at 25°C
  - ± 20 mV from 0°C to 60°C
- Overvoltage protection options from 3.55 V to
- Undervoltage protection with options from 1.0 V to 3.5 V
- Open-wire connection detection
- Overtemperature protection
- Random cell connection
- · Functional safety-capable
- Fixed internal delay timers
- Fixed detections thresholds
- Fixed output drive type for each of COUT and **DOUT** 
  - Active high or active low
  - Active high drive to 6 V
  - Open drain with ability to be pulled up externally to VDD
- Low power consumption I<sub>CC</sub> ≈ 1 µA  $(V_{CELL(ALL)} < V_{OV})$
- Low leakage current per cell input < 100 nA with open wire detection disabled
- Package footprint options:
  - Leaded 24-pin TSSOP with 0.65-mm lead pitch

## 2 Applications

- Protection for Li-ion battery packs used in:
  - Handheld garden tools
  - Handheld power tools
  - Cordless vacuum cleaners
  - UPS battery backup
  - Light electric vehicles (eBike, eScooter, pedal assist bicycles)

# 3 Description

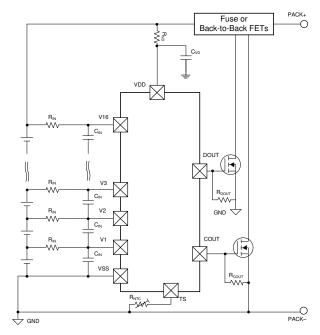
The BQ77216 family of products provides a range of voltage and temperature monitoring including overvoltage (OVP), undervoltage (UVP), open wire (OW), and overtemperature (OT) protection for Liion battery pack systems. Each cell is monitored independently for overvoltage, undervoltage, and open-wire conditions. With the addition of an external NTC thermistor, the device can detect overtemperature conditions.

In the BQ77216 device, an internal delay timer initiated upon detection of an overvoltage, undervoltage. open-wire, or overtemperature condition. Upon expiration of the delay timer, the respective output is triggered into its active state (either high or low, depending on the configuration).

#### **Device Information Table**

PART NUMBER	PACKAGE	BODY SIZE (NOM)
BQ7721600 <sup>(1)</sup>		4.40 mm × 7.80 mm (6.40 mm × 7.80 mm, including leads)

For available catalog packages, see the orderable addendum at the end of the data sheet and the Device Comparison Table.



Simplified Schematic



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# **4 Revision History**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision H (March 2023) to Revision I (July 2023)	Page
Updated the Device Comparison Table	3
Changes from Revision G (July 2022) to Revision H (March 2023)	Page
Updated the Device Comparison Table	3
Changes from Revision F (June 2022) to Revision G (September 2022)	Page
Updated the Device Comparison Table	3
Changes from Revision E (April 2022) to Revision F (June 2022)	Page
Changed the UVP entry for the BQ7721609 device in the Device Comparison Table	3
Changes from Revision D (January 2022) to Revision E (April 2022)	Page
Moved the BQ7721609 and BQ7721610 devices from PRODUCT PREVIEW to Production Data in the Device Comparison Table	



# **5 Description (continued)**

The overvoltage triggers the COUT pin if a fault is detected, and undervoltage triggers the DOUT pin if a fault is detected. If an overtemperature or open-wire fault is detected, then both the DOUT and COUT will be triggered. For quicker production-line testing, the BQ77216 device provides a Customer Test Mode (CTM) with greatly reduced delay time.

# **6 Device Comparison Table**

Table 6-1. BQ77216 Device Comparison

PART NUMBER	T <sub>A</sub>	PACKAGE	PACKAGE DESIGNATOR	OVP (V)	OV HYSTERISIS (V)	OVP DELAY	UVP (V)	UVP DELAY	
BQ7721600	-40°C to 110°C	24-Pin TSSOP	PW	4.325	0.100	1 s	2.25	1 s	
BQ7721602	-40°C to 110°C	24-Pin TSSOP	PW	4.325	0.100	1 s	2.25	1 s	
BQ7721603	-40°C to 110°C	24-Pin TSSOP	PW	4.3	0.100	2 s	2	2 s	
BQ7721605	-40°C to 110°C	24-Pin TSSOP	PW	4.225	0.100	1 s	2.6	1 s	
BQ7721606	-40°C to 110°C	24-Pin TSSOP	PW	4.275	0.100	1 s	2.5	1 s	
BQ7721607	-40°C to 110°C	24-Pin TSSOP	PW	4.25	0.100	4 s	2.5	2 s	
BQ7721609	-40°C to 110°C	24-Pin TSSOP	PW	4.35	0.200	4 s	Disa	bled	
BQ7721610	-40°C to 110°C	24-Pin TSSOP	PW	4.25	0.100	4 s	2.5	2 s	
BQ7721611	-40°C to 110°C	24-Pin TSSOP	PW	3.8	0.200	4 s	1.5	1 s	
BQ7721612	-40°C to 110°C	24-Pin TSSOP	PW	3.6	0.200	2 s	2.0	2 s	
BQ7721613	-40°C to 110°C	24-Pin TSSOP	PW	4.25	0.100	4 s	2.0	2 s	
BQ7721614	-40°C to 110°C	24-Pin TSSOP	PW	3.9	0.100	4 s	1.85	2 s	

Table 6-2. BQ77216 Device Comparison (continued)

Table 6 2. Ber 12 16 Bevice Companion (Continued)									
PART NUMBER	UV HYSTERISIS (V)	OTC (°C)	UTC (°C)	ow	LATCH	OUTPUT DRIVE	TAPE AND REEL		
BQ7721600	0.100	70	NA	Enabled	Disabled	Active Low	BQ7721600PWR		
BQ7721602	0.100	70	NA	Enabled	Disabled	Active High, 6-V Drive	BQ7721602PWR		
BQ7721603	0.100	75	NA	Enabled	Disabled	Active High, 6-V Drive	BQ7721603PWR		
BQ7721605	0.200	75	NA	Disabled	Disabled	Active High, 6-V Drive	BQ7721605PWR		
BQ7721606	0.200	75	NA	Disabled	Disabled	Active High, 6-V Drive	BQ7721606PWR		
BQ7721607	0.100	83	-30	Enabled	Disabled	Active High, 6-V Drive	BQ7721607PWR		
BQ7721609	Disabled	83	NA	Enabled	Disabled	Active High, 6-V Drive	BQ7721609PWR		
BQ7721610	0.100	83	NA	Enabled	Disabled	Active High, 6- V Drive (COUT) Active Low (DOUT)	BQ7721610PWR		
BQ7721611	0.200	70	NA	Disabled	Disabled	Active High, 6-V Drive	BQ7721611PWR		
BQ7721612	0.200	75	NA	Disabled	Disabled	Active Low	BQ7721612PWR		
BQ7721613	0.100	83	-30	Enabled	Disabled	Active High, 6-V Drive	BQ7721613PWR		
BQ7721614	0.100	75	-30	Enabled	Disabled	Active High, 6-V Drive	BQ7721614PWR		



# 7 Pin Configuration and Functions

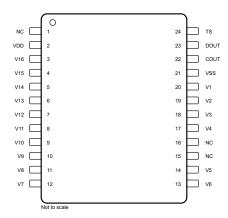


Table 7-1. 24-Lead Pin Functions

NO.	NAME	TYPE	DESCRIPTION
1	NC	_	Not electrically connected and can be left floating
2	VDD	Р	Power supply
3	V16	ı	Sense input for positive voltage of the sixteenth cell from the bottom of the stack
4	V15	I	Sense input for positive voltage of the fifteenth cell from the bottom of the stack
5	V14	ı	Sense input for positive voltage of the fourteenth cell from the bottom of the stack
6	V13	I	Sense input for positive voltage of the thirteenth cell from the bottom of the stack
7	V12	1	Sense input for positive voltage of the twelfth cell from the bottom of the stack
8	V11	1	Sense input for positive voltage of the eleventh cell from the bottom of the stack
9	V10	I	Sense input for positive voltage of the tenth cell from the bottom of the stack
10	V9	ı	Sense input for positive voltage of the ninth cell from the bottom of the stack
11	V8	1	Sense input for positive voltage of the eighth cell from the bottom of the stack
12	V7	1	Sense input for positive voltage of the seventh cell from the bottom of the stack
13	V6	1	Sense input for positive voltage of the sixth cell from the bottom of the stack
14	V5	I	Sense input for positive voltage of the fifth cell from the bottom of the stack
15	NC	_	Not electrically connected and can be left floating
16	NC	_	Not electrically connected and can be left floating
17	V4	ı	Sense input for positive voltage of the fourth cell from the bottom of the stack
18	V3	ı	Sense input for positive voltage of the third cell from the bottom of the stack
19	V2	ı	Sense input for positive voltage of the second cell from the bottom of the stack
20	V1	ı	Sense input for positive voltage of the lowest cell in the stack
21	VSS	Р	Electrically connected to IC ground and negative terminal of the lowest cell in the stack
22	COUT	0	Output drive for overvoltage, open wire, and overtemperature. It can be left floating if not used.
23	DOUT	0	Output drive for undervoltage, open wire, and overtemperature. It can be left floating if not used.
24	TS	I	Temperature sensor input. If not used, leave it NC.
I = Inp	out, O = Outpu	t, P = Po	wer Connection

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# 8 Specifications

# 8.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
Supply voltage range	VDD - VSS	-0.3	85	V
Input voltage renge	Vn - VSS where n = 1 to 16	-0.3	85	V
Input voltage range	TS	-0.3	1.5	V
Output voltage range	COUT - VSS, DOUT - VSS	-0.3	85	V
unctional temperature,T <sub>FUNC</sub>		-40	110	°C
Storage temperature, T <sub>STG</sub>		<b>–65</b>	150	°C

<sup>(1)</sup> Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

## 8.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/ JEDEC JS-001, all pins <sup>(1)</sup>	±2000	V
V <sub>(ESD)</sub>	Electrostatic discriarge	Charged device model (CDM), per ANSI/ESDA/ JEDEC JS-002, all pins	±500	<b>V</b>

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

# 8.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM MAX	UNIT
$V_{DD}$	Supply voltage <sup>(1)</sup>	5	75	V
V	Input voltage range of Vn - Vn-1 where n = 2 to 16 and V1 - VSS	0	5	V
V <sub>IN</sub>	TS	0	1.5	V
V <sub>CTM</sub>	Customer Test Mode Entry V <sub>DD</sub> > V16 + V <sub>CTM</sub>	12	13	V
C <sub>TS</sub>	Total capacitance on the TS Pin		200	pF
T <sub>A</sub>	Ambient temperature	-40	85	°C
TJ	Junction temperature	-65	150	°C

<sup>(1)</sup> V<sub>DD</sub> is equal to top of stack voltage

## 8.4 Thermal Information

		DEVICE	
	THERMAL METRIC(1)	PW (TSSOP)	UNIT
		24 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	97.8	°C/W
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	40.5	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	53.1	°C/W
$\Psi_{JT}$	Junction-to-top characterization parameter	4.3	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	52.7	°C/W



		DEVICE	
	THERMAL METRIC <sup>(1)</sup>	PW (TSSOP)	UNIT
		24 PINS	
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	NA	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

## 8.5 DC Characteristics

Typical values stated where  $T_A$  = 25°C and VDD = 58 V, MIN/MAX values stated where  $T_A$  = -40°C to 85°C and VDD = 5 V to 75 V (unless otherwise noted).

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OVER VO	LTAGE PROTECTION (OV)					
V <sub>OV</sub>	OV Detection Range		3.55		5.1	V
V <sub>OV_STEP</sub>	OV Detection Steps			25		mV
	OV Detection Unitarialis	Selected OV Hysterysis depends on part number. See device selection table for details.		V <sub>OV</sub> – 100		mV
V <sub>OV_HYS</sub>	OV Detection Hysteresis	Selected OV Hysterysis depends on part number. See device selection table for details.		V <sub>OV</sub> – 200		mV
V <sub>OV_ACC</sub>	OV Detection Accuracy	T <sub>A</sub> = 25°C	-10		10	mV
	OV Detection Accuracy	0°C ≤ T <sub>A</sub> ≤ 60°C	-20		20	mV
	OV Detection Accuracy	-40°C ≤ T <sub>A</sub> ≤ 110°C	-50		50	mV
UNDER V	OLTAGE PROTECTION (UV)					
V <sub>UV</sub>	UV Detection Range		1.0		3.5	V
V <sub>UV_STEP</sub>	UV Detection Steps			50		mV
	UV Detection Hysteresis	Selected OV Hysterysis depends on part number. See device selection table for details.		V <sub>UV</sub> + 100		mV
V <sub>UV_HYS</sub>		Selected OV Hysterysis depends on part number. See device selection table for details.		V <sub>UV</sub> + 200		mV
	UV Detection Accuracy	T <sub>A</sub> = 25°C	-30		30	mV
V <sub>UV_ACC</sub>	UV Detection Accuracy	-40 ≤ T <sub>A</sub> ≤ 110°C	-50		50	mV
V <sub>UV_MIN</sub>	UV Detection Disabled Threshold	Vn - Vn-1 where n = 2 to 16 and V1 - VSS	450	500	550	mV
OVER TE	MPERATURE PROTECTION (OT)			,		
T <sub>OT</sub>	OT Detection Range	Available options: 62°C, 65°C, 70°C, 75°C, 80°C, 83°C	62.0		83.0	°C
		62°C		2850		
		65°C		2570		
D	OT Detection External Desistance	70°C		2195		0
R <sub>OT_EXT</sub>	OT Detection External Resistance	75°C		1915		Ω
		80°C		1651		
		83°C		1525		
T <sub>OT_ACC</sub>	OT Detection Accuracy		-5		5	°C

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# 8.5 DC Characteristics (continued)

Typical values stated where  $T_A$  = 25°C and VDD = 58 V, MIN/MAX values stated where  $T_A$  = -40°C to 85°C and VDD = 5 V to 75 V (unless otherwise noted).

o 75 V (unless otherwise noted).  PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT	
				-10		°C	
T <sub>OT_HYS</sub>	OT Detection Hysteresis			4186		Ω	
(2)	,			3530		Ω	
R <sub>NTC</sub>	Internal Pull Up Resistor	After TI Factory Trim	19.5	20	20.6	kΩ	
	RE PROTECTION (OW)	,					
		Vn < Vn-1 where n = 2 to 16		-200		mV	
$V_{OW}$	OW Detection Threshold	V1 - VSS		500		mV	
V <sub>OW_HYS</sub>	OW Detection Hysteresis	Vn < Vn-1 where n = 1 to 16		V <sub>OW</sub> +100		mV	
V <sub>OW ACC</sub>	OW Detection Accuracy	-40 °C ≤ T <sub>A</sub> ≤ 110°C	-25		25	mV	
	AND LEAKAGE CURRENT	,,					
I <sub>CC</sub>	Supply Current	No fault detected.		2	3.5	μA	
		Vn - Vn-1 and V1 - VSS = 4V, where n = 2 to 16, Open Wire Enabled	-0.3		0.3	μA	
I <sub>IN</sub> <sup>(2)</sup>	Input Current at Vx Pins	Vn - Vn-1 and V1 - VSS = 4V, where n = 2 to 16, Open Wire Disabled	-0.1		0.1	μΑ	
OUTPUT	DRIVE, COUT and DOUT, CMOS ACTIV	VE HIGH VERSIONS ONLY		-			
	Output Drive Voltage for COUT and DOUT, Active High 6V	Vn - Vn-1 or V1 - VSS > V <sub>OV</sub> , where n = 2 to 16, VDD = 58 V, I <sub>OH</sub> = 100 μA measured out of COUT, DOUT pin.	6			V	
	Output Drive Voltage for COUT and DOUT, Active High VDD	VDD - $V_{COUT}$ or $V_{DOUT}$ , Vn - Vn-1 or V1 - VSS > $V_{OV}$ , where n = 2 to 16, $I_{OH}$ = 10 $\mu$ A measured out of COUT, DOUT pin.	0	1	1.5	V	
V <sub>OUT_AH</sub>	Output Drive Voltage for COUT and DOUT, Active High 6V	VDD - $V_{COUT}$ or $V_{DOUT}$ , If 15 of 16 cells are short circuited and only one cell remains powered and > $V_{OV}$ , VDD = $V_{X}$ (cell voltage), $I_{OH}$ = 100 $\mu$ A,	0	1	1.5	٧	
	Output Drive Voltage for COUT and DOUT, Active High 6V and VDD	Vn - Vn-1 and V1 - VSS < V <sub>OV</sub> , where n = 2 to 16, VDD = 58 V, I <sub>OH</sub> = 100 μA measured into pin		250	400	mV	
R <sub>OUT_AH</sub>	Internal Pull Up Resistor		80	100	120	kΩ	
I <sub>OUT_AH_</sub> H	OUT Source Current (during OV)	Vn - Vn-1 or V1 - VSS > V <sub>OV</sub> , where n = 2 to 16, VDD = 58 V, OUT = 0V. Measured out of COUT, DOUT pin			4.5	mA	
I <sub>OUT_AH_L</sub>	OUT Sink Current (no OV)	Vn - Vn-1 and V1 - VSS < V <sub>OV</sub> , where n = 2 to 16, VDD = 58 V, OUT = VDD. Measured into COUT, DOUT pin	0.3		3	mA	
OUTPUT	DRIVE, COUT and DOUT, NCH OPEN	DRAIN ACTIVE LOW VERSIONS ONLY					
V <sub>OUT_AL</sub>	Output Drive Voltage for COUT and DOUT, Active Low	Vn - Vn-1 or V1 - VSS > V <sub>OV</sub> , where n = 2 to 16, VDD = 58 V, I <sub>OH</sub> = 100 μA measured into COUT, DOUT pin.		250	400	mV	
I <sub>OUT_AL_L</sub>	OUT Source Current (during OV)	Vn - Vn-1 or V1 - VSS > V <sub>OV</sub> , where n = 2 to 16, VDD = 58 V, OUT = VDD. Measured into COUT, DOUT pin.	0.3		3	mA	
I <sub>OUT_AL_H</sub>	OUT Sink Current (no OV)	Vn - Vn-1 and V1 - VSS < V <sub>OV</sub> , where n = 2 to 16, VDD = 58 V, OUT = VDD. Measured out of COUT, DOUT pin.	n = 2 to 16, VDD = 58 V, OUT = VDD.				

<sup>(1)</sup> Assured by Design. This accuracy assumes the external resistance is within +/- 2% of the R\_OT\_EXT values for the corresponding temperature threshold.

<sup>(2)</sup> Assured by Design.



# 8.6 Timing Requirements

Typical values stated where  $T_A$  = 25°C and VDD = 58 V, MIN/MAX values stated where  $T_A$  = -40°C to 85°C and VDD = 5 V to 85 V (unless otherwise noted).

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
				0.25		s
				0.5		S
t <sub>OV_DELAY</sub>	OV Delay Time			1		S
				2		S
				4		s
t <sub>UV_DELAY</sub>				0.25		S
	UV Delay Time			0.5		S
	OV Delay Time			1		S
				2		S
t <sub>OT_DELAY</sub>	OT Delay Time			4		s
t <sub>OW_DELAY</sub>	OW Delay Time			4		S
t <sub>DELAY_ACC</sub>	Delay Time Accuracy	For 0.25s, 0.5s delays	-128		128	ms
t <sub>DELAY_ACC</sub>	Delay Time Accuracy	For 1s delays	-150		150	ms
t <sub>DELAY_DR</sub>	Delay time drift across operating temp	For all delays other than 0.25s, 0.5s, 1s delays	-10%		10%	
t <sub>CTM_DELAY</sub>	Fault Detection Delay Time during Customer Test Mode	See Customer Test Mode.		50		ms



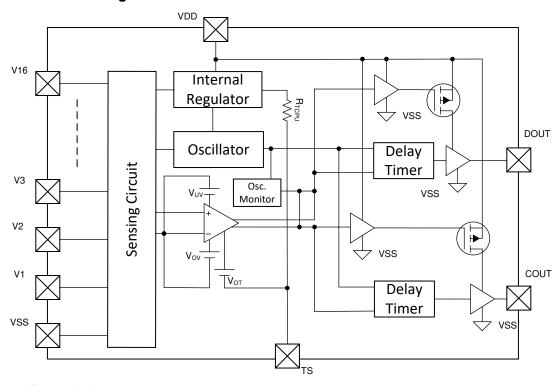
# 9 Detailed Description

## 9.1 Overview

The BQ77216 family of devices provides a range of voltage and temperature monitoring including overvoltage (OVP), undervoltage (UVP), open wire (OW), and overtemperature (OT) protection for Li-ion battery pack systems. Each cell is monitored independently for overvoltage, undervoltage, and open-wire conditions. With the addition of an external NTC thermistor, the device can detect overtemperature conditions. An internal delay timer is initiated upon detection of an overvoltage, undervoltage, open-wire, or overtemperature condition. Upon expiration of the delay timer, the respective output is triggered into its active state (either high or low depending on the configuration). The overvoltage triggers the COUT pin if a fault is detected, and undervoltage triggers the DOUT pin if a fault is detected. If an undertemperature, overtemperature, or open-wire fault is detected, then both the DOUT and COUT are triggered.

For quicker production-line testing, the BQ77216 device provides a Customer Test Mode (CTM) with greatly reduced delay time.

## 9.2 Functional Block Diagram



## 9.3 Feature Description

#### 9.3.1 Voltage Fault Detection

In the BQ77216 device, each cell is monitored independently. Overvoltage is detected by comparing the actual cell voltage to a protection voltage reference,  $V_{OV}$ . If any cell voltage exceeds the programmed OV value, a timer circuit is activated. When the timer expires, the COUT pin goes from inactive to active state. The timer is reset if the cell voltage falls below the recovery threshold ( $V_{OV} - V_{OV\_HYS}$ ). Undervoltage is detected by comparing the actual cell voltage to a protection voltage reference,  $V_{UV}$ . If any cell voltage falls below the programmed UV value, a timer circuit is activated. When the timer expires, the DOUT pin goes from inactive to active state. The timer is reset if the cell voltage rises below the recovery threshold ( $V_{UV} + V_{UV\_HYS}$ ).



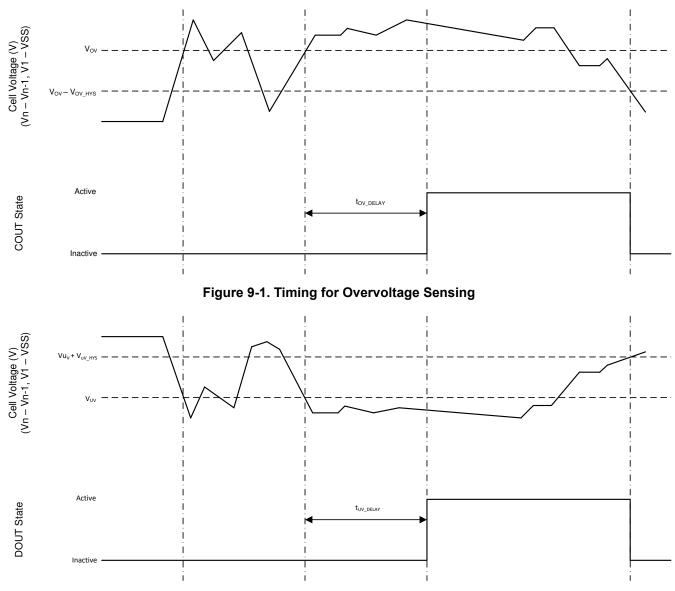


Figure 9-2. Timing for Undervoltage Sensing

#### 9.3.2 Open Wire Fault Detection

In the BQ77216 device, each cell input is monitored independently to determine if the input is connected to a cell or not by applying a 50- $\mu$ A pull down current to ground that is activated for 128  $\mu$ s every 128 ms. If the device detects that Vn < Vn-1 – V<sub>OW</sub> V, then a timer is activated. When the timer expires, the COUT and DOUT pins go from an inactive to active state. The timer is reset if the cell input rises above below the recovery threshold (V<sub>OW</sub> + V<sub>OW\_HYS</sub>).

# 9.3.3 Temperature Fault Detection

In the BQ77216 device, the TS pin is ratiometrically monitored with an internal pull up resistance  $R_{NTC}$ . Overtemperature is detected by evaluating the TS input voltage to determine the external resistance falls below a protection resistance,  $R_{OT\_EXT}$ . If the resistance falls below the programmed OT value, a timer circuit is activated. When the timer expires, the COUT and DOUT pins go from inactive to active state. The timer is reset if the resistance rises above the recovery threshold ( $R_{OT} + R_{OT\_HYS}$ ). If external capacitance is added to the TS pin, it needs to be within the spec limit shown in recommended operating conditions.



#### **Note**

Texas Instruments does not recommend adding an external capacitor to the TS pin. The capacitance on this pin will affect the TS measurement accuracy if greater than  $C_{TS}$ .

#### 9.3.4 Oscillator Health Check

The device can detect if the internal oscillator slows down below the f<sub>OSC\_FAULT</sub> threshold. When this occurs then the COUT and DOUT go from inactive to active state. If the oscillator returns to normal then the fault recovers.

#### 9.3.5 Sense Positive Input for Vx

This is an input to sense each single battery cell voltage. A series resistor and a capacitor across the cell for each input is required for noise filtering and stable voltage monitoring.

#### 9.3.6 Output Drive, COUT and DOUT

These pins serve as the fault signal outputs, and may be ordered in either active HIGH with drive to 6V or active LOW options configured through internal OTP.

The COUT and DOUT will respond per the following table when a fault is detected, if the specific fault is enabled.

Table 3-1.1 dult Detection vs COOT and DOOT Action								
FAULT Detected	COUT	DOUT						
Overvoltage	Active	Inactive						
Undervoltage	Inactive	Active						
Open Wire	Active	Active						
Over Temperature	Active	Active						
Oscillator Health	Active	Active						

Table 9-1 Fault Detection vs COUT and DOUT Action

#### 9.3.7 The LATCH Function

The device can be enabled to latch the fault signal, which effectively disables the recovery functions of all fault detections. The only way to recover from a fault state when the latch is enabled is a POR of the device.

## 9.3.8 Supply Input, VDD

This pin is the unregulated input power source for the IC. A series resistor is connected to limit the current, and a capacitor is connected to ground for noise filtering.

#### 9.4 Device Functional Modes

#### 9.4.1 NORMAL Mode

When COUT and DOUT are inactive (no fault detected) the device operates in NORMAL mode and device is monitoring for voltage, open wire and temperature faults.

The COUT and DOUT pins are inactive and if configured:

- · Active high is low.
- · Active low is being externally pulled up and is an open drain.

#### 9.4.2 FAULT Mode

FAULT mode is entered if the COUT or DOUT pins are activated. The OUT pin will either pull high internally, if configured as active high, or will be pulled low internally, if configured as active low. When COUT and DOUT are deactivated the device returns to NORMAL mode.

#### 9.4.3 Customer Test Mode

Customer Test Mode (CTM) helps to reduce test time for checking the delay timer parameter once the circuit is implemented in the battery pack. To enter CTM, VDD should be set to at least  $V_{CTM}$  higher than V16 (see Figure 9-3). The delay timer is greater than 10 ms, but considerably shorter than the timer delay in normal operation. To



exit Customer Test Mode, remove the VDD to a V16 voltage differential of 10 V so that the decrease in this value automatically causes an exit.

#### **CAUTION**

Avoid exceeding any Absolute Maximum Voltages on any pins when placing the part into Customer Test Mode. Also avoid exceeding Absolute Maximum Voltages for the individual cell voltages (VCn–VCn-1) and (V1–VSS). Stressing the pins beyond the rated limits may cause permanent damage to the device.

Figure 9-3 shows the timing for the Customer Test Mode.

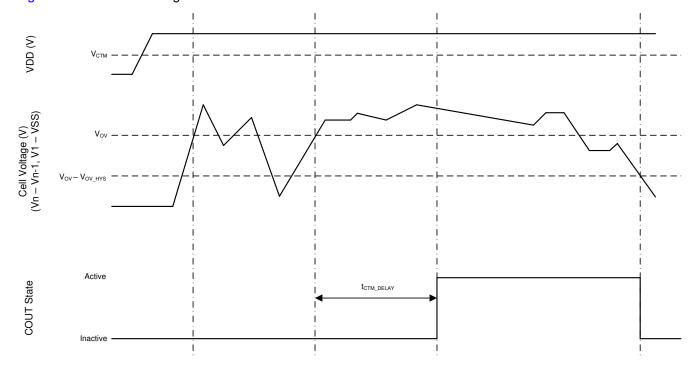


Figure 9-3. Timing for Customer Test Mode

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# 10 Application and Implementation

## Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

# 10.1 Application Information

Changes to the ranges stated in Table 10-1 will impact the accuracy of the cell measurements.

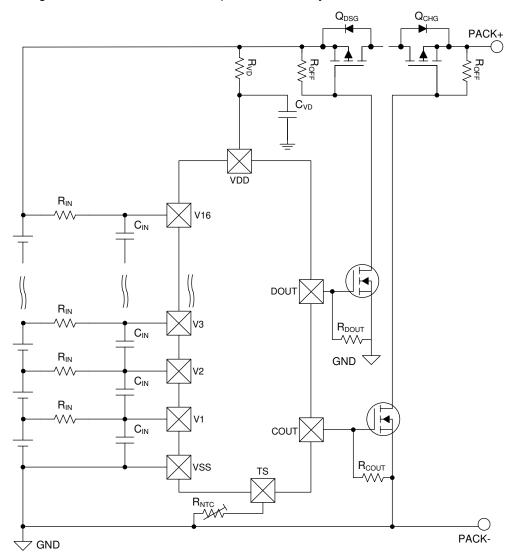


Figure 10-1. Application Configuration

#### 10.1.1 Design Requirements

Changes to the ranges stated in Table 10-1 will impact the accuracy of the cell measurements. Figure 10-1 shows each external component.

Table 10-1. Parameters

PARAMETER	EXTERNAL COMPONENT	MIN	NOM	MAX	UNIT
Voltage monitor filter resistance	R <sub>IN</sub>	900	1000	1100	Ω



PARAMETER	EXTERNAL COMPONENT	MIN	NOM	MAX	UNIT
Voltage monitor filter capacitance	C <sub>IN</sub>	0.01		0.1	μF
Supply voltage filter resistance	R <sub>VD</sub>	100	300	1K	Ω
Supply voltage filter capacitance	C <sub>VD</sub>	0.05	0.1	1	μF

#### Note

The device is calibrated using an  $R_{IN}$  value = 1 k $\Omega$ . Using a value other than this recommended value changes the accuracy of the cell voltage measurements and  $V_{OV}$  trigger level.

#### 10.1.2 Detailed Design Procedure

Figure 10-2 shows the measurement for current consumption for the product for both VDD and Vx.

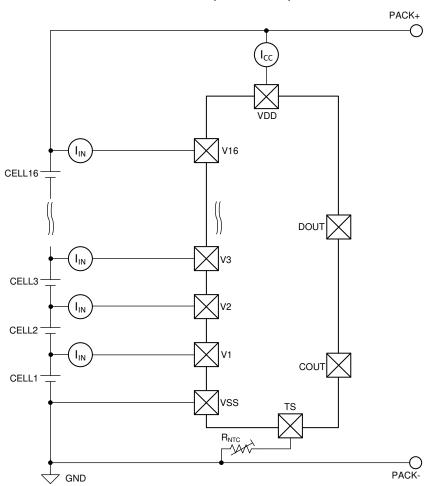


Figure 10-2. Configuration for IC Current Consumption Test

# 10.1.2.1 Cell Connection Sequence

The BQ77216 device can be connected to the array of cells in any order without damaging the device.

During cell attachment, the device could detect a fault if the cells are not connected within a fault detection delay period. If this occurs, then COUT and/or DOUT could transition from inactive to active. Both COUT and DOUT can be tied to VSS or VDD to prevent any change in output state during cell attach.

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## 10.2 Systems Example

In this application example, the choice of a FUSE or FETs is required on the COUT and DOUT pins—configured as an active high drive to 6-V outputs.

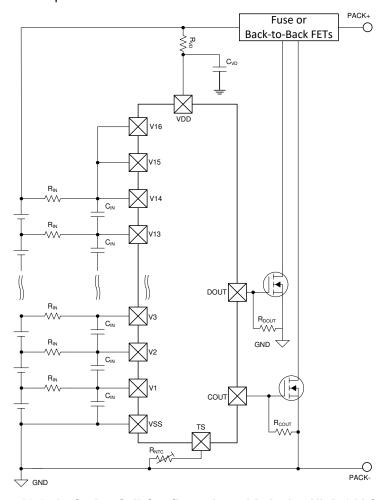


Figure 10-3. 14-Series Cell Configuration with Active High 6-V Option

When paring with the BQ769x2 or BQ76940 devices, the top cell must be used. For the BQ77216 device to drive the CHG and DSG FETs, the active high 6-V option is preferred. Its COUT and DOUT are controlling two N-CH FETs to jointly control the CHG and DSG FETs with the monitoring device. For such joint architecture, the open-wire feature of the BQ77216 device may be affected if the primary protector or monitor device is actively measuring the cells. Care is needed to ensure the  $V_{OW}$  spec of the BQ77216 device is met or to choose a version of the BQ77216 device with open wire disabled. When working with a BQ769x2 device, the LOOPSLOW setting of the BQ769x2 device should be set to 0x11 to ensure the BQ77216  $V_{OW}$  spec is met.



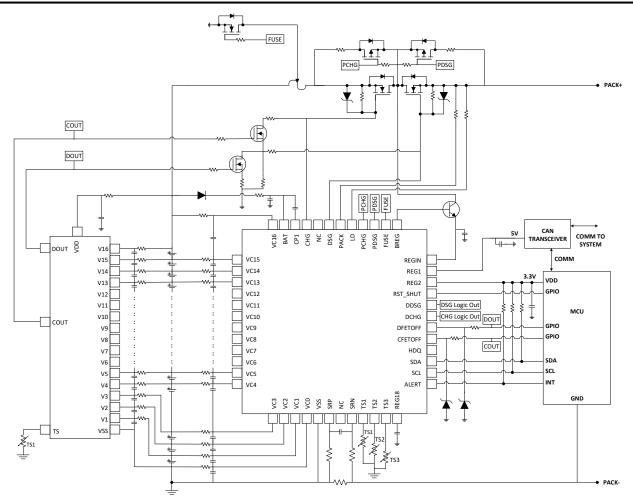


Figure 10-4. BQ77216 with BQ76952

# 11 Power Supply Recommendations

The maximum power supply of this device is 85 V on VDD.



# 12 Layout

# 12.1 Layout Guidelines

- Ensure the RC filters for the Vn and VDD pins are placed as close as possible to the target terminal.
- The VSS pin should be routed to the CELL

   terminal.

# 12.2 Layout Example

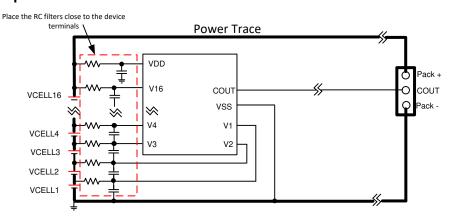


Figure 12-1. Example Layout



# 13 Device and Documentation Support

# 13.1 Third-Party Products Disclaimer

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# 13.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

## 13.3 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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## 13.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 13.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

# 14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
BQ7721600PWR	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7721600	Samples
BQ7721602PWR	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7721602	Samples
BQ7721603PWR	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7721603	Samples
BQ7721605PWR	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 110	BQ7721605	Samples
BQ7721606PWR	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 110	BQ7721606	Samples
BQ7721607PWR	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 110	BQ7721607	Samples
BQ7721609PWR	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 110	BQ7721609	Samples
BQ7721610PWR	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 110	BQ7721610	Samples
BQ7721611PWR	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 110	BQ7721611	Samples
BQ7721612PWR	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 110	BQ7721612	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: Til defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.



# **PACKAGE OPTION ADDENDUM**

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(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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# TAPE AND REEL INFORMATION



# TAPE DIMENSIONS + K0 - P1 - B0 W Cavity - A0 -

A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
BQ7721600PWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1
BQ7721602PWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1
BQ7721603PWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1
BQ7721605PWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1
BQ7721606PWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1
BQ7721607PWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1
BQ7721609PWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1
BQ7721610PWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1
BQ7721611PWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1
BQ7721612PWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1



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\*All dimensions are nominal

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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
BQ7721600PWR	TSSOP	PW	24	2000	356.0	356.0	35.0
BQ7721602PWR	TSSOP	PW	24	2000	356.0	356.0	35.0
BQ7721603PWR	TSSOP	PW	24	2000	356.0	356.0	35.0
BQ7721605PWR	TSSOP	PW	24	2000	356.0	356.0	35.0
BQ7721606PWR	TSSOP	PW	24	2000	356.0	356.0	35.0
BQ7721607PWR	TSSOP	PW	24	2000	356.0	356.0	35.0
BQ7721609PWR	TSSOP	PW	24	2000	356.0	356.0	35.0
BQ7721610PWR	TSSOP	PW	24	2000	356.0	356.0	35.0
BQ7721611PWR	TSSOP	PW	24	2000	356.0	356.0	35.0
BQ7721612PWR	TSSOP	PW	24	2000	356.0	356.0	35.0



SMALL OUTLINE PACKAGE



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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